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CENTRAL FAX CENTERLISTING OF CLAIMS:

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This listing of claims will replace all prior versions of claims in the application:

- 1 1. (Withdrawn) A method of forming high aspect ratio copper structures, comprising:
 - 3 depositing a photoresist;
 - 4 performing a reactive ion etch (RIE) process to form a trench;
 - 5 depositing Cu;
 - 6 performing single chemical mechanical polishing (CMP) process to remove selected amounts of said photoresist and Cu.
- 1 2. (Withdrawn) A method as in claim 1 wherein said single CMP is performed using a slurry comprising: SiO₂, Ammonium Persulfate, and Benzotriazole (BTA).
- 1 3. (Withdrawn) A method as in claim 1 further comprising depositing Al₂O₃.
- 1 4. (Withdrawn) A method as in claim 1 further comprising depositing a SiO₂ hard mask, and wherein said CMP process removes said hard mask material at substantially the same rate as said photoresist, and Cu.
- 1 5. (Withdrawn) A method as in claim 1 further comprising depositing a Ta barrier layer, and wherein said CMP process removes said Ta at substantially the same rate as said photoresist, and Cu.

1 6. (Original) A method for forming a Cu coil for use in a magnetic head,
2 comprising:
3 Forming a magnetic pole structure;
4 depositing a photoresist;
5 depositing a hard mask;
6 patterning said hard mask to define a coil pattern;
7 performing a material removal process to form at least one trench according to
8 said coil pattern;
9 depositing Ta
10 depositing Cu; and
11 performing a chemical mechanical polishing (CMP) process using a slurry
12 comprising:
13 Amonium Persulfate, Benzotriazole (BTA), and SiO₂.

1 7. (Original) method as in claim 6, wherein said depositing Cu includes sputter
2 depositing a seed layer of Cu and then electroplating Cu.

1 8. (Original) A method as in claim 6 further comprising adjusting a ratio of
2 Ammonium Persulfate and Benzotriazole (BTA) so that said CMP process
3 removes material from said photoresist, hard mask, Ta, and Cu at substantially the
4 same rate.

- 1 9. (Original) A method as in claim 6 further comprising forming a magnetic
- 2 pedestal and a magnetic back gap extending from said pole structure and wherein
- 3 a portion of said photoresist is deposited between said magnetic pedestal and said
- 4 magnetic back gap.

- 1 10. (Original) A method as in claim 10, wherein said magnetic pedestal and said
- 2 back gap comprise NiFe.

- 1 11. (Original) A method as in claim 6, further comprising performing said CMP
- 2 process sufficiently to form a substantially planar surface including said
- 3 photoresist, and said Cu.

- 1 12. (Original) A method as in claim 6 further comprising performing said CMP
- 2 process sufficiently to form a substantially planar surface including said
- 3 photoresist, said Cu and said Ta.

- 1 13. (Original) A method as in claim 6, further comprising hard baking said
- 2 photoresist before performing said material removal process.

- 1 14. (Original) A method as in claim 6 wherein said material removal process
- 2 comprises reactive ion etching (RIE).

1 15. (Original) A method as in claim 6 further comprising depositing alumina
2 (Al₂O₃).

1 16. (Original) A method as in claim 6
2 further comprising:
3 forming a magnetic pedestal and a magnetic back gap extending
4 from said pole structure; and
5 depositing alumina (Al₂O₃) and wherein:
6 a portion of said photoresist is deposited between said
7 magnetic pedestal and said magnetic back gap; and
8 said material removal process removes said material from
9 said magnetic pedestal, magnetic back gap, photoresist, hard mask,
10 Ta, alumina and Cu at substantially the same rate.

1 17. (Withdrawn) A slurry for use in chemical mechanical polishing, comprising:
2 SiO₂;
3 Amonium Persulfate ((NH₄)₂S₂O₈); and
4 Benzotriazole BTA.

18. (Withdrawn) A method of forming a small Cu structure, comprising:
depositing a photoresist;
performing a material removal process form a cavity in said photoresist;
depositing Cu; and

performing a chemical mechanical polishing process using a slurry comprising:

SiO₂ Ammonium Persulfate, and Benzotriazole (BTA).